

**Silicon NPN Power Transistor**

**KSD5060**

**DESCRIPTION**

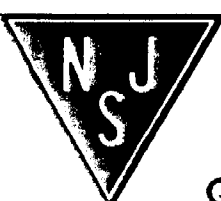
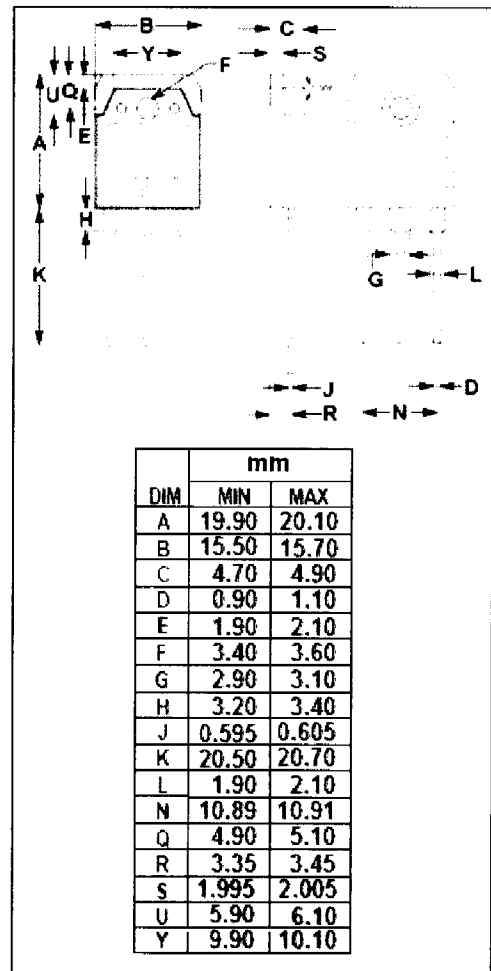
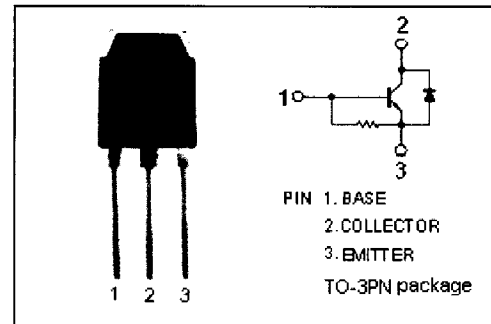
- High Breakdown Voltage-  
 :  $V_{CBO} = 1500V$  (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

**APPLICATIONS**

- Designed for color TV horizontal output applications

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	2.5	A
$I_{CP}$	Collector Current-Peak	10	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ C$	80	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



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## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2A; I_B=0.6A$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2A; I_B=0.6A$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=800V; I_E=0$			10	$\mu A$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=4V; I_C=0$	40		200	mA
$h_{FE}$	DC Current Gain	$I_C=0.5A; V_{CE}=5V$	8			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.5A; V_{CE}=10V$		3		MHz
$V_{ECF}$	C-E Diode Forward Voltage	$I_F=2.5A$			2.0	V
$t_f$	Fall Time	$I_C=2A, I_{B1}=0.6A; I_{B2}=-1.2A$ $R_L=100\Omega; V_{CC}=200V$			0.4	$\mu s$